In re Appln. of KAZUHIRO TANAKA Application No. 09/965,803

CLAIM AMENDMENTS

Claims 1-13 (Cancelled).

14. (Currently Amended) A method of chemical mechanical polishing of an object comprising:

supplying a slurry to a polishing apparatus including a polisher and the object to be polished;

measuring particle information, including at least one of dispersion of particles and distribution of particle sizes, of the slurry being supplied to <u>and directly used in polishing of the object in</u> the polishing apparatus; and

controlling polishing speed at which the object is being polished, based on the particle information.

- 15. (Currently Amended) The method according to claim 14 including controlling the polishing speed of the object by adjusting a physical variable of the polisher.
- 16. (Previously Presented) The method according to claim 15, wherein the physical variable is at least one of a rotation speed of the polisher, rotation speed of the object, and force applied by the polisher to the object.
- 17. (Previously Presented) The method according to claim 14 including supplying a mixture of a first slurry and a second slurry to the polishing apparatus as the slurry.
- 18. (Currently Amended) The method according to claim 17 including controlling mixing ratio between the first slurry and the second slurry <u>based</u> on the particle information.
 - 19. (Currently Amended) The method according to claim 18, further comprising: detecting the polishing speed at which the object is <u>being</u> polished; and controlling the mixing ratio based on the polishing speed.
- 20. (Currently Amended) A method of chemical mechanical polishing of an object comprising:

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supplying a slurry to a polishing apparatus including a polisher and the object to be polished;

measuring particle information, including at least one of dispersion of particle particles and distribution of particle sizes, of the slurry being supplied to and directly used in polishing of the object in the polishing apparatus; and

controlling polishing time of the object, based on the particle information.